

SILICON RECTIFIERS

VOLTAGE RANGE: 100 V
CURRENT: 2.0 A

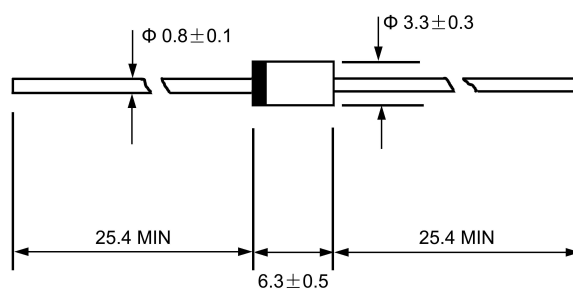
FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned with Freon,Alcohol,Isopropanop and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case:JEDEC DO-15,molded plastic
- ◇ Terminals: Axial lead ,solderable per MIL- STD-202,Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Mounting position: Any

DO - 15



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		2AH4	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	100	V
Maximum RMS voltage	V_{RMS}	70	V
Maximum DC blocking voltage	V_{DC}	100	V
Maximum average forward rectified current 9.5mm lead length, @ $T_A=75^\circ C$	$I_{F(AV)}$	2.0	A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	I_{FSM}	40	A
Maximum instantaneous forward voltage @2.0 A	V_F	4.0	V
Maximum reverse current @ $T_A=25^\circ C$ at rated DC blocking voltage @ $T_A=100^\circ C$	I_R	5.0 50	μA
Typical junction capacitance (Note1)	C_J	40	pF
Typical thermal resistance (Note2)	$R_{\theta JA}$	18	$^\circ C/W$
Operating junction temperature range	T_J	- 55---- +150	$^\circ C$
Storage temperature range	T_{STG}	- 55---- +150	$^\circ C$

NOTE:1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Thermal resistance from junction to ambient.

RATINGS AND CHARACTERISTIC CURVES

FIG.1 TYPICAL FORWARD CHARACTERISTICS

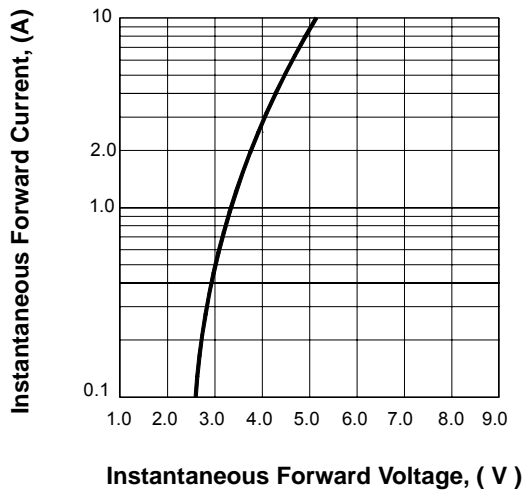


FIG.2 FORWARD DERATING CURVE

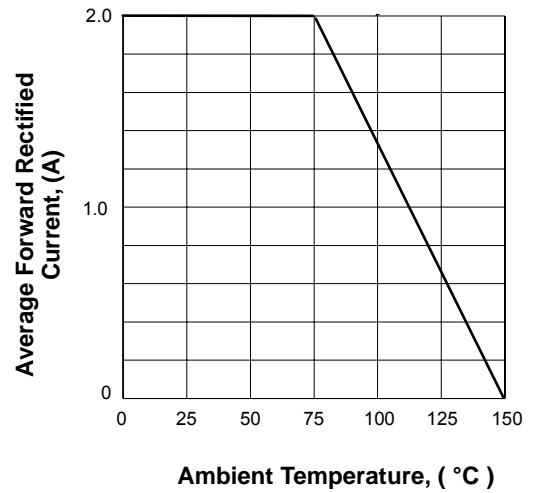


FIG.3 TYPICAL REVERSE CHARACTERISTICS

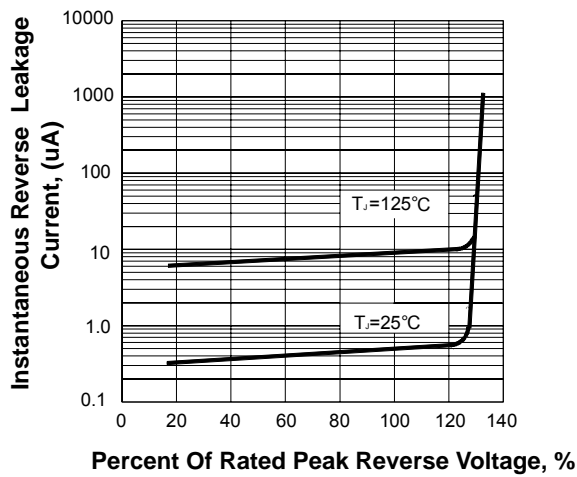


FIG.4 PEAK FORWARD SURGE CURRENT

